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| <input type="checkbox"/> | L8 | l1 and l2 and l3 and l4 and l5 and l7 | 14 |
| <input type="checkbox"/> | L7 | (heat\$3 or anneal\$3) | 325809 |
| <input type="checkbox"/> | L6 | (heat43 or anneal\$3) | 47889 |
| <input type="checkbox"/> | L5 | (barrier adj layer\$)near6 (resist\$3 or immun\$6 r insuscept\$4) | 806 |
| <input type="checkbox"/> | L4 | L3 | 771 |
| <input type="checkbox"/> | L3 | (Ge or germanium) near4 (surface\$2) | 771 |
| <input type="checkbox"/> | L2 | (insulator near4 substrate\$) | 6461 |
| <input type="checkbox"/> | L1 | (Si near2 Ge or SiGe or silicon adj germanium) | 11779 |

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Search Results - Record(s) 1 through 10 of 14 returned.

☐ 1. Document ID: US 20050130424 A1

L8: Entry 1 of 14

File: PGPB

Jun 16, 2005

PGPUB-DOCUMENT-NUMBER: 20050130424

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20050130424 A1

TITLE: Use of hydrogen implantation to improve material properties of silicon-germanium-on-insulator material made by thermal diffusion

PUBLICATION-DATE: June 16, 2005

INVENTOR-INFORMATION:

| NAME | CITY | STATE | COUNTRY | RULE-47 |
|---------------------|------------------|-------|---------|---------|
| Bedell, Stephen W. | Wappingers Falls | NY | US | |
| Fogel, Keith E. | Mohegan Lake | NY | US | |
| Sadana, Devendra K. | Pleasantville | NY | US | |

US-CL-CURRENT: 438/689

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KNIC | Draw De |
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|------|---------|
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|------|---------|

☐ 2. Document ID: US 20050095803 A1

L8: Entry 2 of 14

File: PGPB

May 5, 2005

PGPUB-DOCUMENT-NUMBER: 20050095803

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20050095803 A1

TITLE: Formation of silicon-germanium-on-insulator (SGOI) by an integral high temperature SIMOX-Ge interdiffusion anneal

PUBLICATION-DATE: May 5, 2005

INVENTOR-INFORMATION:

| NAME | CITY | STATE | COUNTRY | RULE-47 |
|---------------------|------------------|-------|---------|---------|
| Bedell, Stephen W. | Wappingers Falls | NY | US | |
| Fogel, Keith E. | Mohegan Lake | NY | US | |
| Sadana, Devendra K. | Pleasantville | NY | US | |
| Shahidi, Ghavam G. | Pound Ridge | NY | US | |

US-CL-CURRENT: 438/407

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw De |
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|------|---------|
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|------|---------|

☐ 3. Document ID: US 20050093100 A1

L8: Entry 3 of 14

File: PGPB

May 5, 2005

PGPUB-DOCUMENT-NUMBER: 20050093100

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20050093100 A1

TITLE: Method for fabricating SiGe-on-insulator (SGOI) and Ge-on-insulator (GOI) substrates

PUBLICATION-DATE: May 5, 2005

INVENTOR-INFORMATION:

| NAME | CITY | STATE | COUNTRY | RULE-47 |
|---------------------|------------------|-------|---------|---------|
| Chen, Tze-chiang | Yorktown Heights | NY | US | |
| Cohen, Guy M. | Mohegan Lake | NY | US | |
| Reznicek, Alexander | Mount Kisco | NY | US | |
| Sadana, Devendra K. | Pleasantville | NY | US | |
| Shahidi, Ghavam G. | Pound Ridge | NY | US | |

US-CL-CURRENT: 257/616

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw De |
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|------|---------|
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|------|---------|

☐ 4. Document ID: US 20050048778 A1

L8: Entry 4 of 14

File: PGPB

Mar 3, 2005

PGPUB-DOCUMENT-NUMBER: 20050048778

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20050048778 A1

TITLE: Use of thin SOI to inhibit relaxation of SiGe layers

PUBLICATION-DATE: March 3, 2005

INVENTOR-INFORMATION:

| NAME | CITY | STATE | COUNTRY | RULE-47 |
|---------------------|------------------|-------|---------|---------|
| Bedell, Stephen W. | Wappingers Falls | NY | US | |
| Chen, Huajie | Wappingers Falls | NY | US | |
| Fogel, Keith E. | Mohegan Lake | NY | US | |
| Sadana, Devendra K. | Pleasantville | NY | US | |

US-CL-CURRENT: 438/689; 117/4, 257/E21.129

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw. Da |
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|------|----------|
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☐ 5. Document ID: US 20050003229 A1

L8: Entry 5 of 14

File: PGPB

Jan 6, 2005

PGPUB-DOCUMENT-NUMBER: 20050003229

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20050003229 A1

TITLE: Defect reduction by oxidation of silicon

PUBLICATION-DATE: January 6, 2005

INVENTOR-INFORMATION:

| NAME | CITY | STATE | COUNTRY | RULE-47 |
|-------------------------|------------------|-------|---------|---------|
| Bedell, Stephen W. | Wappingers Falls | NY | US | |
| Chen, Huajie | Wappingers Falls | NY | US | |
| Domenicucci, Anthony G. | New Paltz | NY | US | |
| Fogel, Keith E. | Mohegan Lake | NY | US | |
| Sadana, Devendra K. | Pleasantville | NY | US | |

US-CL-CURRENT: 428/641; 257/E21.561, 438/514

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw. Da |
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|------|----------|
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|------|----------|

☐ 6. Document ID: US 20040259334 A1

L8: Entry 6 of 14

File: PGPB

Dec 23, 2004

PGPUB-DOCUMENT-NUMBER: 20040259334

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040259334 A1

TITLE: High-quality SGOI by annealing near the alloy melting point

PUBLICATION-DATE: December 23, 2004

INVENTOR-INFORMATION:

| NAME | CITY | STATE | COUNTRY | RULE-47 |
|-------------------------|------------------|-------|---------|---------|
| Bedell, Stephen W. | Wappingers Falls | NY | US | |
| Chen, Huajie | New Paltz | NY | US | |
| Domenicucci, Anthony G. | Mohegan Lake | NY | US | |
| Fogel, Keith E. | Clinton Corners | NY | US | |
| Murphy, Richard J. | Pleasantville | NY | US | |
| Sadana, Devendra K. | | | US | |

US-CL-CURRENT: 438/478

| | | | | | | | | | | | | |
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|-----|--------|
| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KMC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|-----|--------|

☐ 7. Document ID: US 20040242006 A1

L8: Entry 7 of 14

File: PGPB

Dec 2, 2004

PGPUB-DOCUMENT-NUMBER: 20040242006

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040242006 A1

TITLE: SiGe lattice engineering using a combination of oxidation, thinning and epitaxial regrowth

PUBLICATION-DATE: December 2, 2004

INVENTOR-INFORMATION:

| NAME | CITY | STATE | COUNTRY | RULE-47 |
|---------------------|------------------|-------|---------|---------|
| Bedell, Stephen W. | Wappingers Falls | NY | US | |
| Chen, Huajie | Wappingers Falls | NY | US | |
| Fogel, Keith E. | Mohegan lake | NY | US | |
| Sadana, Devendra K. | Pleasantville | NY | US | |

US-CL-CURRENT: 438/692

| | | | | | | | | | | | | |
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|-----|--------|
| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KMC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|-----|--------|

☐ 8. Document ID: US 20040241460 A1

L8: Entry 8 of 14

File: PGPB

Dec 2, 2004

PGPUB-DOCUMENT-NUMBER: 20040241460

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040241460 A1

TITLE: Formation of silicon-Germanium-on-insulator (SGOI) by an integral high temperature SIMOX-Ge interdiffusion anneal

PUBLICATION-DATE: December 2, 2004

INVENTOR-INFORMATION:

| NAME | CITY | STATE | COUNTRY | RULE-47 |
|---------------------|------------------|-------|---------|---------|
| Bedell, Stephen W. | Wappingers Falls | NY | US | |
| de Souza, Joel P. | Putnam Valley | NY | US | |
| Fogel, Keith E. | Mohegan Lake | NY | US | |
| Sadana, Devendra K. | Pleasantville | NY | US | |
| Shahidi, Ghavam G. | Pound Ridge | NY | US | |

US-CL-CURRENT: 428/446; 428/450, 428/641, 438/479

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw. De |
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|------|----------|
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☐ 9. Document ID: US 20040241459 A1

L8: Entry 9 of 14

File: PGPB

Dec 2, 2004

PGPUB-DOCUMENT-NUMBER: 20040241459

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040241459 A1

TITLE: Formation of silicon-germanium-on-insulator (SGOI) by an integral high temperature SIMOX-Ge interdiffusion anneal

PUBLICATION-DATE: December 2, 2004

INVENTOR-INFORMATION:

| NAME | CITY | STATE | COUNTRY | RULE-47 |
|---------------------|------------------|-------|---------|---------|
| Bedell, Stephen W. | Wappingers Falls | NY | US | |
| Fogel, Keith E. | Mohegan Lake | NY | US | |
| Sadana, Devendra K. | Pleasantville | NY | US | |
| Shahidi, Ghavam G. | Pound Ridge | NY | US | |

US-CL-CURRENT: 428/446; 428/641

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw. De |
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|------|----------|
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|------|----------|

☐ 10. Document ID: US 20040238885 A1

L8: Entry 10 of 14

File: PGPB

Dec 2, 2004

PGPUB-DOCUMENT-NUMBER: 20040238885

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040238885 A1

TITLE: High-quality SGOI by oxidation near the alloy melting temperature

PUBLICATION-DATE: December 2, 2004

INVENTOR-INFORMATION:

| NAME | CITY | STATE | COUNTRY | RULE-47 |
|-------------------------|------------------|-------|---------|---------|
| Bedell, Stephen W. | Wappingers Falls | NY | US | |
| Domenicucci, Anthony G. | New Paltz | NY | US | |
| Fogel, Keith E. | Mohegan Lake | NY | US | |
| Sadana, Devendra K. | Pleasantville | NY | US | |

US-CL-CURRENT: 257/347

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw. De |
|------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|------|----------|
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Day : Tuesday
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Inventor Name Search Result

Your Search was:

Last Name = FOGEL

First Name = KEITH

| Application# | Patent# | Status | Date Filed | Title | Inventor Name 46 |
|-----------------|------------|--------|------------|--|------------------|
| <u>60421480</u> | Not Issued | 159 | 10/24/2002 | LAND GRID ARRAY FABRICATION USING ELASTOMER CORE AND CONDUCTING METAL SHELL OR MESH | FOGEL, KEITH E. |
| <u>60026088</u> | Not Issued | 159 | 09/13/1996 | WAFER SCALE HIGH DENSITY PROBE ASSEMBLY | FOGEL, KEITH E. |
| <u>60020000</u> | Not Issued | 159 | 06/21/1996 | FOAMED ELASTOMERS FOR WAFER PROBING APPLICATIONS AND INTERPOSER CONNECTORS | FOGEL, KEITH E. |
| <u>11039602</u> | Not Issued | 030 | 01/19/2005 | FORMATION OF SILICON-GERMANIUM-ON-INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-GE INTERDIFFUSION ANNEAL | FOGEL, KEITH E. |
| <u>11029921</u> | Not Issued | 030 | 01/05/2005 | HIGH-QUALITY SGOI BY OXIDATION NEAR THE ALLOY MELTING TEMPERATURE | FOGEL, KEITH E. |
| <u>10993270</u> | Not Issued | 020 | 11/19/2004 | PATTERNED SOI BY OXYGEN IMPLANTATION AND ANNEALING | FOGEL, KEITH E. |
| <u>10984212</u> | Not Issued | 030 | 11/09/2004 | FORMATION OF SILICON-GERMANIUM-ON-INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-GE INTERDIFFUSION ANNEAL | FOGEL, KEITH E. |
| <u>10982411</u> | Not Issued | 030 | 11/05/2004 | USE OF HYDROGEN IMPLANTATION TO IMPROVE MATERIAL PROPERTIES OF SILICON-GERMANIUM-ON-INSULATOR MATERIAL MADE BY THERMAL DIFFUSION | FOGEL, KEITH E. |

| | | | | | |
|-----------------|------------|-----|------------|---|-----------------|
| <u>10932598</u> | Not Issued | 020 | 09/02/2004 | METHOD OF PRODUCING SILICON-GERMANIUM-ON-INSULATOR MATERIAL USING UNSTRAINED GE-CONTAINING SOURCE LAYERS | FOGEL, KEITH E. |
| <u>10928473</u> | Not Issued | 030 | 08/27/2004 | ELECTRICAL CONNECTOR DESIGN AND CONTACT GEOMETRY AND METHOD OF USE THEREOF AND METHODS OF FABRICATION THEREOF | FOGEL, KEITH |
| <u>10890765</u> | Not Issued | 030 | 07/14/2004 | ION IMPLANTATION FOR SUPPRESSION OF DEFECTS IN ANNEALED SIGE LAYERS | FOGEL, KEITH E. |
| <u>10883887</u> | Not Issued | 030 | 07/02/2004 | STRAINED SILICON-ON-INSULATOR BY ANODIZATION OF A BURIED P+ SILICON GERMANIUM LAYER | FOGEL, KEITH E. |
| <u>10883883</u> | Not Issued | 041 | 07/02/2004 | ULTRA-THIN, HIGH QUALITY STRAINED SILICON-ON-INSULATOR FORMED BY ELASTIC STRAIN TRANSFER | FOGEL, KEITH E. |
| <u>10855915</u> | Not Issued | 041 | 05/27/2004 | HIGH-QUALITY SGOI BY ANNEALING NEAR THE ALLOY MELTING POINT | FOGEL, KEITH E. |
| <u>10824289</u> | Not Issued | 030 | 04/14/2004 | METHOD OF CREATING HIGH-QUALITY RELAXED SIGE-ON-INSULATOR FOR STRAINED SI CMOS APPLICATIONS | FOGEL, KEITH E. |
| <u>10818572</u> | Not Issued | 030 | 04/06/2004 | METHOD OF FORMING HIGH-QUALITY RELAXED SIGE ALLOY LAYERS ON BULK SI SUBSTRATES | FOGEL, KEITH E. |
| <u>10815103</u> | Not Issued | 030 | 03/31/2004 | INTERCONNECTIONS FOR FLIP-CHIP USING LEAD-FREE SOLDERS AND HAVING REACTION BARRIER LAYERS | FOGEL, KEITH E. |
| <u>10768341</u> | Not Issued | 030 | 01/30/2004 | HIGH ELECTRICAL QUALITY BURIED OXIDE IN SIMOX | FOGEL, KEITH E. |
| <u>10715288</u> | Not Issued | 061 | 11/17/2003 | INTERPOSER WITH ELECTRICAL CONTACT BUTTON AND METHOD | FOGEL, KEITH E. |
| <u>10710826</u> | Not Issued | 030 | 08/05/2004 | METHOD OF FORMING STRAINED SILICON MATERIALS WITH IMPROVED | FOGEL, KEITH |

| | | | | | |
|-----------------|----------------|-----|------------|---|-----------------|
| | | | | THermal CONDUCTIVITY | |
| <u>10696601</u> | <u>6861158</u> | 150 | 10/29/2003 | FORMATION OF SILICON-GERMANIUM-ON-INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-GE INTERDIFFUSION ANNEAL | FOGEL, KEITH E. |
| <u>10674648</u> | Not Issued | 030 | 09/30/2003 | SOI BY OXIDATION OF POROUS SILICON | FOGEL, KEITH E. |
| <u>10674647</u> | Not Issued | 030 | 09/30/2003 | THIN BURIED OXIDES BY LOW-DOSE OXYGEN IMPLANTATION INTO MODIFIED SILICON | FOGEL, KEITH E. |
| <u>10664714</u> | <u>6825102</u> | 150 | 09/18/2003 | METHOD OF IMPROVING THE QUALITY OF DEFECTIVE SEMICONDUCTOR MATERIAL | FOGEL, KEITH E. |
| <u>10662028</u> | Not Issued | 030 | 09/12/2003 | FORMATION OF A SILICON GERMANIUM-ON-INSULATOR STRUCTURE BY OXIDATION OF A BURIED POROUS SILICON LAYER | FOGEL, KEITH E. |
| <u>10654232</u> | Not Issued | 071 | 09/03/2003 | USE OF THIN SOI TO INHIBIT RELAXATION OF SIGE LAYERS | FOGEL, KEITH E. |
| <u>10654231</u> | <u>6803240</u> | 150 | 09/03/2003 | METHOD OF MEASURING CRYSTAL DEFECTS IN THIN SI/SIGE BILAYERS | FOGEL, KEITH E. |
| <u>10610612</u> | Not Issued | 030 | 07/01/2003 | DEFECT REDUCTION BY OXIDATION OF SILICON | FOGEL, KEITH E. |
| <u>10448954</u> | Not Issued | 041 | 05/30/2003 | SIGE LATTICE ENGINEERING USING A COMBINATION OF OXIDATION, THINNING AND EPITAXIAL REGROWTH | FOGEL, KEITH E. |
| <u>10448948</u> | Not Issued | 041 | 05/30/2003 | HIGH QUALITY SGOI BY OXIDATION NEAR THE ALLOY MELTING TEMPERATURE | FOGEL, KEITH E. |
| <u>10448947</u> | <u>6855436</u> | 150 | 05/30/2003 | FORMATION OF SILICON-GERMANIUM-ON-INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-GE INTERDIFFUSION ANNEAL | FOGEL, KEITH E. |
| <u>10341819</u> | <u>6717217</u> | 150 | 01/14/2003 | ULTIMATE SIMOX | FOGEL, KEITH E. |
| <u>10336147</u> | <u>6878611</u> | 150 | 01/02/2003 | PATTERNED-STRAINED SILICON FOR HIGH | FOGEL, KEITH E. |

| | | | | | |
|-----------------|----------------|-----|------------|--|---------------------|
| | | | | PERFORMANCE CIRCUITS | |
| <u>10334220</u> | <u>6800518</u> | 150 | 12/30/2002 | FORMATION OF PATTERNED SILICON-ON-INSULATOR (SOI)/SILICON-ON-NOTHING (SON) COMPOSITE STRUCTURE BY POROUS SI ENGINEERING | FOGEL, KEITH E. |
| <u>10300189</u> | Not Issued | 092 | 11/20/2002 | RELAXED, LOW-DEFECT SGOI FOR STRAINED SI CMOS APPLICATIONS | FOGEL, KEITH E. |
| <u>10196611</u> | <u>6841457</u> | 150 | 07/16/2002 | USE OF HYDROGEN IMPLANTATION TO IMPROVE MATERIAL PROPERTIES OF SILICON-GERMANIUM-ON-INSULATOR MATERIAL MADE BY THERMAL DIFFUSION | FOGEL, KEITH E. |
| <u>10055138</u> | <u>6805962</u> | 150 | 01/23/2002 | METHOD OF CREATING HIGH-QUALITY RELAXED SIGE-ON-INSULATOR FOR STRAINED SI CMOS APPLICATIONS | FOGEL, KEITH E. |
| <u>09861596</u> | <u>6541356</u> | 150 | 05/21/2001 | THE ULTIMATE SIMOX | FOGEL, KEITH E. |
| <u>09861590</u> | <u>6846727</u> | 150 | 05/21/2001 | PATTERNED SOI BY OXYGEN IMPLANTATION AND ANNEALING | FOGEL, KEITH E. |
| <u>09251988</u> | Not Issued | 092 | 02/17/1999 | STRUCTURAL DESIGN AND PROCESSES TO CONTROL PROBE POSITION ACCURACY IN A WAFER TEST PROBE ASSEMBLY | FOGEL, KEITH E. |
| <u>09081342</u> | <u>6525551</u> | 150 | 05/19/1998 | PROBE STRUCTURES FOR TESTING ELECTRICAL INTERCONNECTIONS TO INTEGRATED CIRCUIT ELECTRONIC DEVICES | FOGEL, KEITH EDWARD |
| <u>08425639</u> | Not Issued | 161 | 04/20/1995 | HIGH TEMPERATURE CHIP TEST PROBE | FOGEL, KEITH E. |
| <u>08425543</u> | Not Issued | 161 | 04/20/1995 | HIGH DENSITY INTEGRAL TEST PROBE AND FABRICATION METHOD | FOGEL, KEITH E. |
| <u>08224383</u> | Not Issued | 166 | 04/07/1994 | INTEGRAL RIGID CHIP TEST PROBE | FOGEL, KEITH E. |
| <u>07485016</u> | <u>4975079</u> | 250 | 02/23/1990 | CONNECTOR ASSEMBLY FOR CHIP TESTING | FOGEL, KEITH |

Inventor Search Completed: No Records to Display.

Day : Tuesday

Date: 7/12/2005

Time: 11:27:35

PALM INTRANET

Inventor Name Search Result

Your Search was:

Last Name = BEDELL

First Name = STEPHEN

| Application# | Patent# | Status | Date Filed | Title | Inventor Name 48 |
|-----------------|------------|--------|------------|--|--------------------|
| <u>60236549</u> | Not Issued | 159 | 09/29/2000 | METHOD OF TRANSPORTING HYDROGEN TO SUB-SURFACE REGION OR CRYSTALLINE INTERFACE WHILE MINIMIZING LATTICE DAMAGE | BEDELL, STEPHEN W. |
| <u>10982411</u> | Not Issued | 030 | 11/05/2004 | USE OF HYDROGEN IMPLANTATION TO IMPROVE MATERIAL PROPERTIES OF SILICON-GERMANIUM-ON-INSULATOR MATERIAL MADE BY THERMAL DIFFUSION | BEDELL, STEPHEN W. |
| <u>10943354</u> | Not Issued | 041 | 09/17/2004 | METHOD FOR PREVENTING SIDEWALL CONSUMPTION DURING OXIDATION OF SGOI ISLANDS | BEDELL, STEPHEN W. |
| <u>10932598</u> | Not Issued | 020 | 09/02/2004 | METHOD OF PRODUCING SILICON-GERMANIUM-ON-INSULATOR MATERIAL USING UNSTRAINED GE-CONTAINING SOURCE LAYERS | BEDELL, STEPHEN W. |
| <u>10905477</u> | Not Issued | 030 | 01/06/2005 | METHOD OF CREATING A GE-RICH CHANNEL LAYER FOR HIGH-PERFORMANCE CMOS CIRCUITS | BEDELL, STEPHEN W. |
| <u>10890765</u> | Not Issued | 030 | 07/14/2004 | ION IMPLANTATION FOR SUPPRESSION OF DEFECTS IN ANNEALED SIGE LAYERS | BEDELL, STEPHEN W. |
| <u>10883887</u> | Not Issued | 030 | 07/02/2004 | STRAINED SILICON-ON-INSULATOR BY ANODIZATION OF A BURIED P+ SILICON GERMANIUM LAYER | BEDELL, STEPHEN W. |

| | | | | | |
|-----------------|------------|-----|------------|--|--------------------|
| <u>10883883</u> | Not Issued | 041 | 07/02/2004 | ULTRA-THIN, HIGH QUALITY STRAINED SILICON-ON-INSULATOR FORMED BY ELASTIC STRAIN TRANSFER | BEDELL, STEPHEN W. |
| <u>10855915</u> | Not Issued | 041 | 05/27/2004 | HIGH-QUALITY SGOI BY ANNEALING NEAR THE ALLOY MELTING POINT | BEDELL, STEPHEN W. |
| <u>10710826</u> | Not Issued | 030 | 08/05/2004 | METHOD OF FORMING STRAINED SILICON MATERIALS WITH IMPROVED THERMAL CONDUCTIVITY | BEDELL, STEPHEN W. |
| <u>10710255</u> | 6893936 | 150 | 06/29/2004 | METHOD OF FORMING STRAINED SI/SIGE ON INSULATOR WITH SILICON GERMANIUM BUFFER | BEDELL, STEPHEN W. |
| <u>10685636</u> | Not Issued | 041 | 10/15/2003 | TECHNIQUES FOR LAYER TRANSFER PROCESSING | BEDELL, STEPHEN W. |
| <u>10664714</u> | 6825102 | 150 | 09/18/2003 | METHOD OF IMPROVING THE QUALITY OF DEFECTIVE SEMICONDUCTOR MATERIAL | BEDELL, STEPHEN W. |
| <u>10662028</u> | Not Issued | 030 | 09/12/2003 | FORMATION OF A SILICON GERMANIUM-ON-INSULATOR STRUCTURE BY OXIDATION OF A BURIED POROUS SILICON LAYER | BEDELL, STEPHEN W. |
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| <u>10604989</u> | 6875982 | 150 | 08/29/2003 | AN ELECTRON MICROSCOPE MAGNIFICATION STANDARD PROVIDING PRECISE CALIBRATION IN THE MAGNIFICATION RANGE 5000X-2000,000X | BEDELL, STEPHEN W. |
| <u>10448947</u> | 6855436 | 150 | 05/30/2003 | FORMATION OF SILICON-GERMANIUM-ON-INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-GE INTERDIFFUSION ANNEAL | BEDELL, STEPHEN W. |
| <u>10336147</u> | 6878611 | 150 | 01/02/2003 | PATTERNED STRAINED SILICON FOR HIGH PERFORMANCE CIRCUITS | BEDELL, STEPHEN W. |

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| <u>10196611</u> | 6841457 | 150 | 07/16/2002 | USE OF HYDROGEN IMPLANTATION TO IMPROVE MATERIAL PROPERTIES OF SILICON-GERMANIUM-ON- INSULATOR MATERIAL MADE BY THERMAL DIFFUSION | BEDELL, STEPHEN W. |
| <u>08816012</u> | 5922109 | 150 | 03/11/1997 | GAS DRYING PROCESS USING GLYCOL SOLUTION SOLUBILITY SUPPRESSANTS | BEDELL, STEPHEN A. |
| <u>08360890</u> | Not Issued | 164 | 12/21/1994 | OXALATE CONTROL | BEDELL, STEPHEN A. |
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| <u>07964323</u> | 5320816 | 150 | 10/21/1992 | PROCESS FOR ABSORPTION OF SULFUR DIOXIDE AND NITRIC OXIDE FROM FLUE GAS | BEDELL, STEPHEN A. |
| <u>07744157</u> | Not Issued | 166 | 08/13/1991 | COMPOSITION AND METHOD FOR SIMULTANEOUS ABSORPTION OF SULFUR DIOXIDE AND NITRIC OXIDE | BEDELL, STEPHEN A. |
| <u>07623313</u> | 5167941 | 150 | 12/06/1990 | QUATERNARY POLYAMINES AS SULFITE OXIDATION INHIBITORS IN AMINE SCRUBBING OF SO ₂ | BEDELL, STEPHEN A. |
| <u>07592402</u> | 5338778 | 150 | 10/03/1990 | REMOVAL OF HYDROGEN SULFIDE FROM FLUID STREAMS | BEDELL, STEPHEN A. |
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| <u>07149777</u> | <u>4808284</u> | 150 | 01/29/1988 | PROCESS FOR THE RECOVERY OF ALKANOLAMINES FROM THEIR HEAT-STABLE SALTS FORMED DURING ABSORBENT THERMAL REGENERATIVE STEP OF GAS CONDITIONING PROCESSES | BEDELL, STEPHEN A. |
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| <u>06831969</u> | <u>4891205</u> | 150 | 02/24/1986 | STABILIZED CHELATING AGENTS FOR REMOVING HYDROGEN SULFIDE | BEDELL, STEPHEN A. |
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| <u>06807419</u> | <u>4632912</u> | 150 | 12/10/1985 | POLYMER SUPPORTED ZIEGLER-NATTA CATALYSTS | BEDELL, STEPHEN A. |
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| <u>06801255</u> | Not Issued | 161 | 11/25/1985 | DRILLING GEOTHERMAL WELLS WITH REMOVAL OF H2S | BEDELL, STEPHEN A. |

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| <u>11081271</u> | Not Issued | 030 | 03/16/2005 | METHOD OF MAKING STRAINED SEMICONDUCTOR TRANSISTORS HAVING LATTICE-MISMATCHED SEMICONDUCTOR REGIONS UNDERLYING SOURCE AND DRAIN REGIONS | CHEN, HUAJIE |
| <u>11037622</u> | Not Issued | 030 | 01/18/2005 | STRUCTURE AND METHOD FOR MANUFACTURING STRAINED SILICON DIRECTLY-ON-INSULATOR SUBSTRATE WITH HYBRID CRYSTALLINE ORIENTATION AND DIFFERENT STRESS LEVELS | CHEN, HUAJIE |
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| <u>10905598</u> | Not | 030 | 01/12/2005 | IN SITU DOPED EMBEDDED | CHEN, HUAJIE |

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| <u>10249563</u> | <u>6780695</u> | 150 | 04/18/2003 | BICMOS INTEGRATION SCHEME WITH RAISED EXTRINSIC BASE | CHEN, HUAJIE |
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